

- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

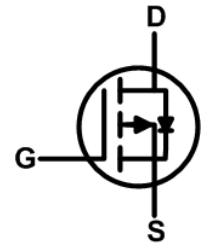
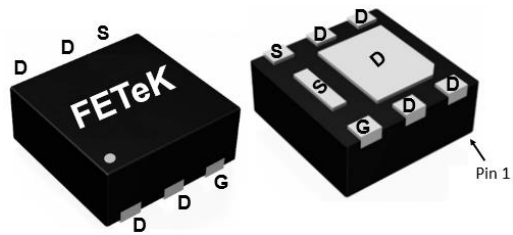
**Product Summary**


BVDSS	RDSON	ID
-30V	32mΩ	-8A

**Description**

The FKCD3113 combines advanced trench MOSFET technology with a low resistance package to provide extremely low RDSON. This device is ideal for load switch and battery protection applications.

The FKCD3113 meet the RoHS and Green Product requirement with full function reliability approved.

**DFN2x2 Pin Configuration**

**Absolute Maximum Ratings**

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	-30	V
$V_{GS}$	Gate-Source Voltage	±20	V
$I_D@T_A=25^\circ\text{C}$	Continuous Drain Current, $V_{GS}$ @ -10V <sup>1</sup>	-8	A
$I_D@T_A=70^\circ\text{C}$	Continuous Drain Current, $V_{GS}$ @ -10V <sup>1</sup>	-6.3	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	-32	A
$P_D@T_A=25^\circ\text{C}$	Total Power Dissipation <sup>3</sup>	2.8	W
$T_{STG}$	Storage Temperature Range	-55 to 150	°C
$T_J$	Operating Junction Temperature Range	-55 to 150	°C

**Thermal Data**

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient <sup>1</sup> (t≤10s)	---	45	°C/W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient <sup>1</sup>	---	80	°C/W

**Electrical Characteristics ( $T_J=25^\circ\text{C}$ , unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-30	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance <sup>2</sup>	$V_{GS}=-10V, I_D=-8A$	---	26	32	m $\Omega$
		$V_{GS}=-4.5V, I_D=-5A$	---	43	53	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=-250\mu A$	-1.2	--	-2.5	V
$I_{DSS}$	Drain-Source Leakage Current	$V_{DS}=-24V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	1	$\mu A$
		$V_{DS}=-24V, V_{GS}=0V, T_J=55^\circ\text{C}$	---	---	5	
$I_{GSS}$	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	$\pm 100$	nA
$g_{fs}$	Forward Transconductance	$V_{DS}=-5V, I_D=-8A$	---	19	---	S
$R_g$	Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1\text{MHz}$		15	---	$\Omega$
$Q_g$	Total Gate Charge (-4.5V)	$V_{DS}=-20V, V_{GS}=-4.5V, I_D=-6A$	---	9.8	---	nC
$Q_{gs}$	Gate-Source Charge		---	2.2	---	
$Q_{gd}$	Gate-Drain Charge		---	3.4	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=-24V, V_{GS}=-10V, R_G=3.3\Omega, I_D=-1A$	---	16.4	---	ns
$T_r$	Rise Time		---	20.2	---	
$T_{d(off)}$	Turn-Off Delay Time		---	55	---	
$T_f$	Fall Time		---	10	---	
$C_{iss}$	Input Capacitance	$V_{DS}=-15V, V_{GS}=0V, f=1\text{MHz}$	---	930	---	$\mu F$
$C_{oss}$	Output Capacitance		---	148	---	
$C_{rss}$	Reverse Transfer Capacitance		---	115	---	

**Diode Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$I_S$	Continuous Source Current <sup>1,4</sup>	$V_G=V_D=0V$ , Force Current	---	---	-6	A
$V_{SD}$	Diode Forward Voltage <sup>2</sup>	$V_{GS}=0V, I_S=-1A, T_J=25^\circ\text{C}$	---	---	-1.2	V

Note :

- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width  $\leq 300\mu s$  , duty cycle  $\leq 2\%$
- 3.The power dissipation is limited by  $150^\circ\text{C}$  junction temperature
- 4.The data is theoretically the same as  $I_D$  and  $I_{DM}$  , in real applications , should be limited by total power dissipation.

Typical Characteristics

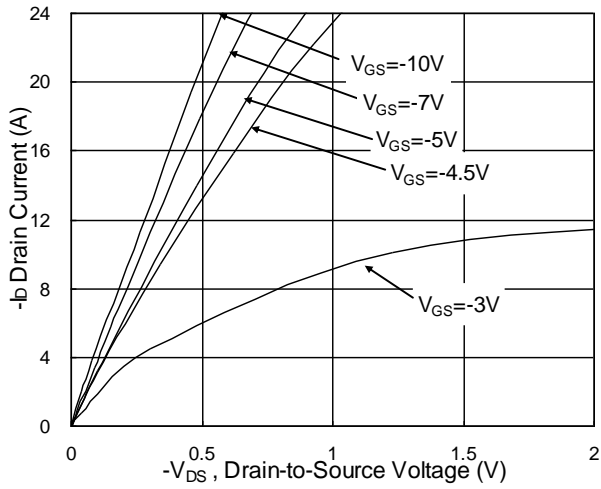


Fig.1 Typical Output Characteristics

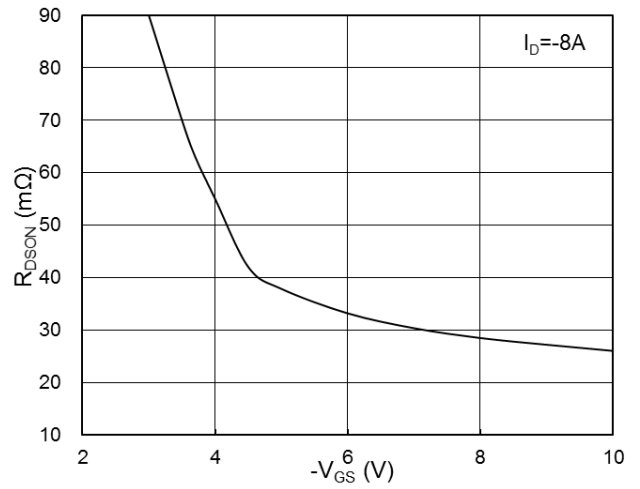


Fig.2 On-Resistance vs G-S Voltage

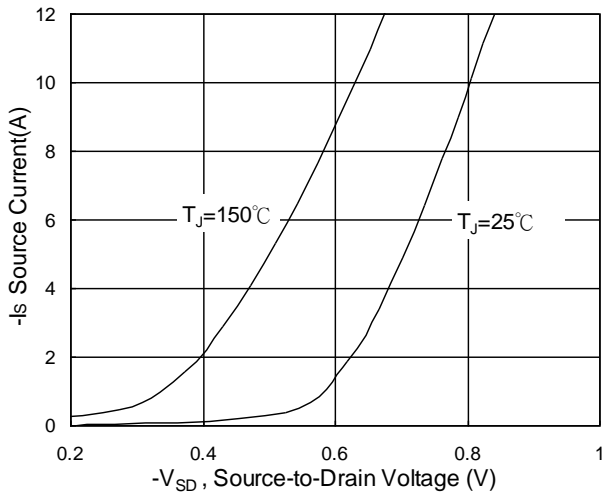


Fig.3 Source-Drain Forward Characteristics

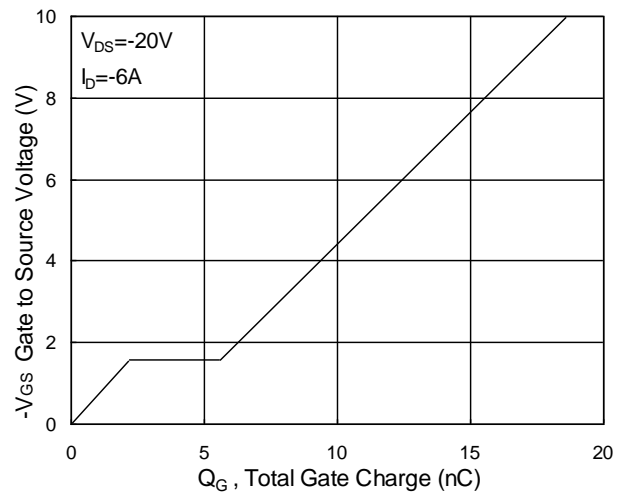


Fig.4 Gate-Charge Characteristics

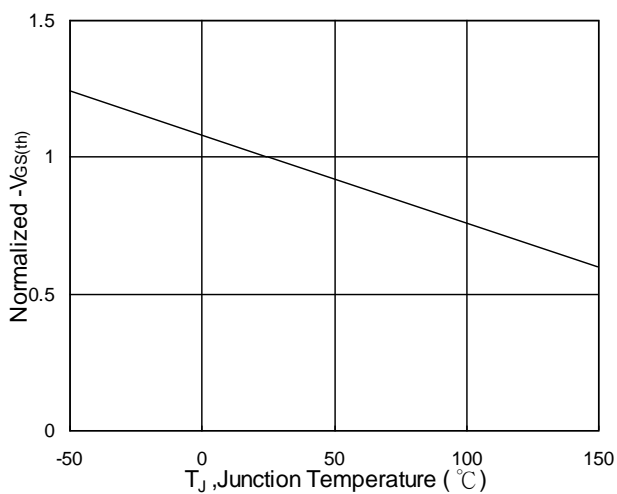


Fig.5 Normalized  $V_{GS(th)}$  vs  $T_J$

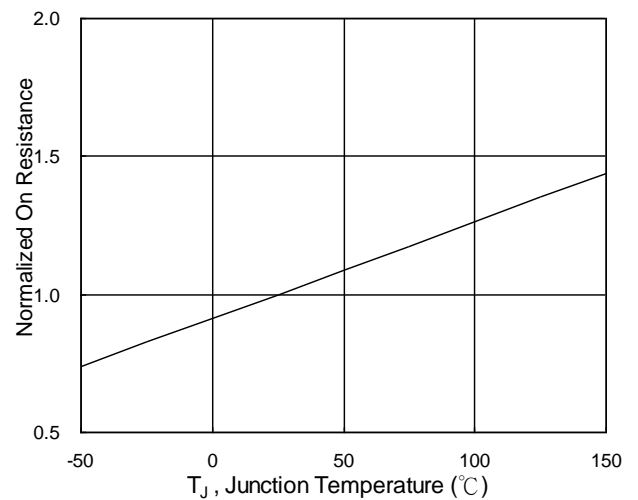


Fig.6 Normalized  $R_{DS(on)}$  vs  $T_J$

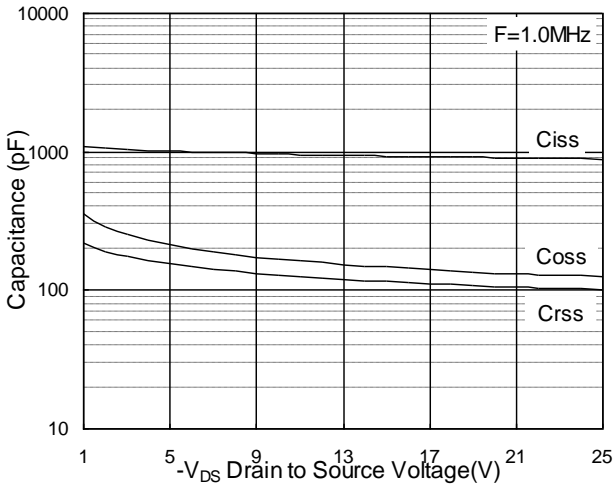


Fig.7 Capacitance

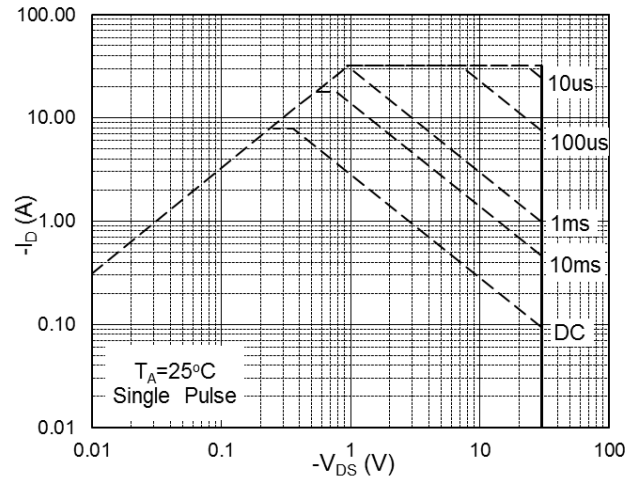


Fig.8 Safe Operating Area

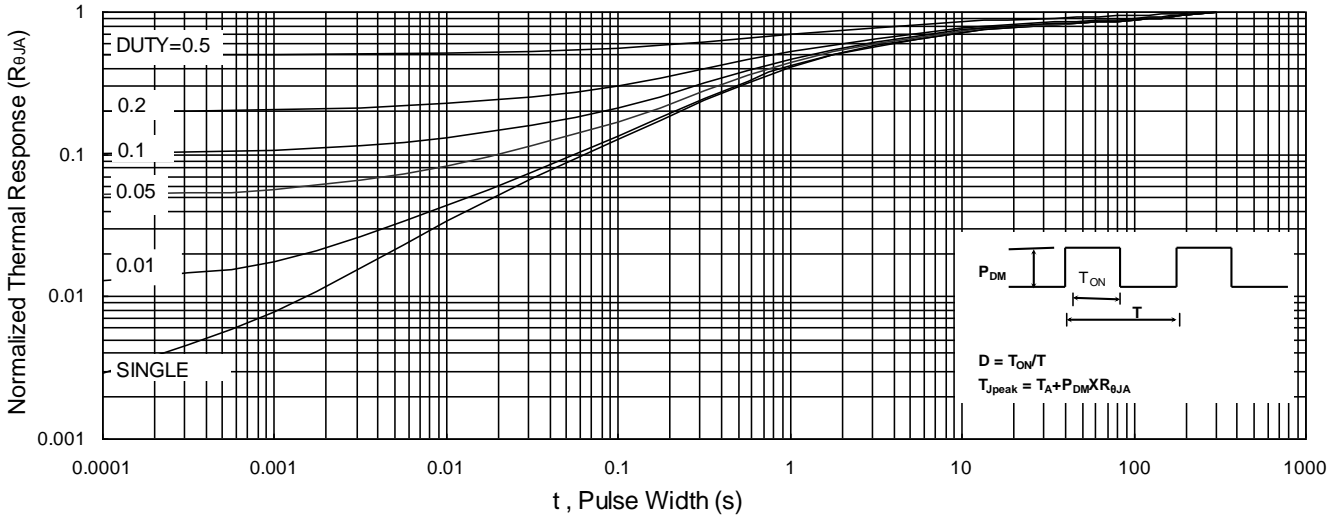


Fig.9 Normalized Maximum Transient Thermal Impedance

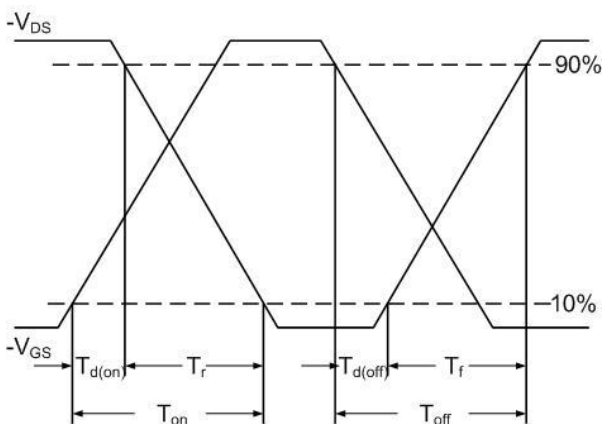


Fig.10 Switching Time Waveform

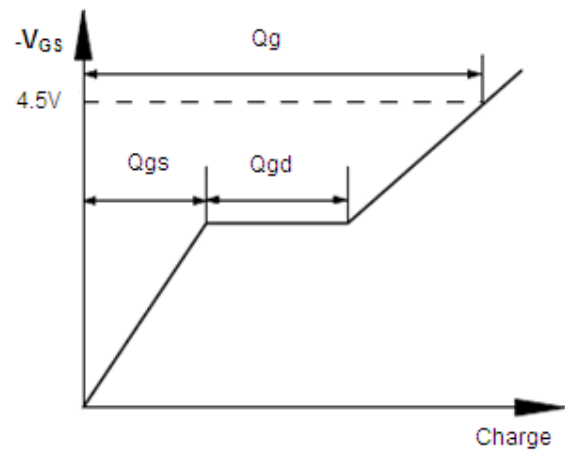


Fig.11 Gate Charge Waveform